

15.45/6059

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re the Application of: ) Group Art Unit: 2811  
TAKEUCHI )  
Serial No. 09/930,365 ) Examiner: Wu  
Filed: June 19, 2001 )  
For: METHODS FOR MANUFACTURING )  
SEMICONDUCTOR DEVICES AND )  
SEMICONDUCTOR DEVICES HAVING )  
TRENCH ISOLATION REGIONS )

#5  
PreAmotta  
FJONES  
5-29-02

**PRELIMINARY AMENDMENT**

Assistant Commissioner for Patents  
Washington, DC 20231

Dear Sir:

Please enter the following.

IN THE CLAIMS:

Please amend claim 26 as follows:

26. (amended) A method as in claim 19, wherein the dielectric layer is formed using high density plasma chemical vapor deposition.

**Remarks**

Claims 1-31 are pending. Applicant has amended claim 26 for clarity. Claim 26, as amended, depends from claim 19. Examination is respectfully requested.

Attached to this paper is a marked-up version of the changes to the claims made by the present amendment. The attached page is captioned "Version With Markings to Show Changes Made."